Abstract of the Disclosure:

In a method for forming a channel zone in field-effect transistors, a polysilicon layer is patterned above the channel zone to be formed. The polysilicon layer serves as a mask substrate for the subsequent doping of the channel zone. The expedient patterning of the polysilicon layer with holes in a gate region and pillars in a source region enables the channel zone to be doped more lightly. In another embodiment, the novel method is used for a channel width shading of a PMOS transistor cell.

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